

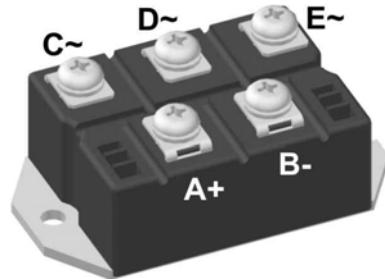
Standard Rectifier Module

| 3~ Rectifier | |
|--------------|----------|
| V_{RRM} | = 1800 V |
| I_{DAV} | = 125 A |
| I_{FSM} | = 1200 A |

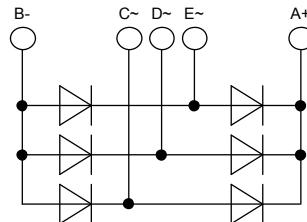
3~ Rectifier Bridge

Part number

VUO110-18NO7



E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

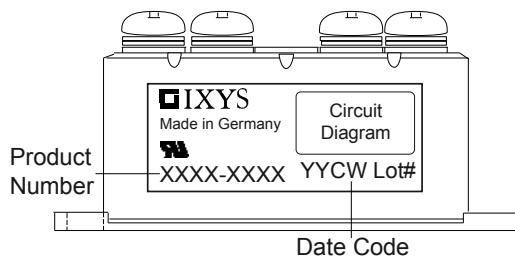
Package: PWS-E

- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Rectifier

| Symbol | Definition | Conditions | Ratings | | | |
|-------------------|--|--|---|------|------------------------------|--------------------|
| | | | min. | typ. | max. | |
| V_{RSM} | max. non-repetitive reverse blocking voltage | $T_{VJ} = 25^\circ C$ | | | 1900 | V |
| V_{RRM} | max. repetitive reverse blocking voltage | $T_{VJ} = 25^\circ C$ | | | 1800 | V |
| I_R | reverse current | $V_R = 1800 V$ $V_R = 1800 V$ | $T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$ | | 100 2 | μA mA |
| V_F | forward voltage drop | $I_F = 50 A$ $I_F = 150 A$ $I_F = 50 A$ $I_F = 150 A$ | $T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$ | | 1.13 1.46 1.04 1.47 | V V |
| I_{DAV} | bridge output current | $T_C = 110^\circ C$ rectangular $d = \frac{1}{3}$ | $T_{VJ} = 150^\circ C$ | | 125 | A |
| V_{FO} r_F | threshold voltage slope resistance } for power loss calculation only | | $T_{VJ} = 150^\circ C$ | | 0.79 4.5 | V $m\Omega$ |
| R_{thJC} | thermal resistance junction to case | | | | 0.7 | K/W |
| R_{thCH} | thermal resistance case to heatsink | | | | 0.3 | K/W |
| P_{tot} | total power dissipation | | $T_C = 25^\circ C$ | | 175 | W |
| I_{FSM} | max. forward surge current | $t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine | $T_{VJ} = 45^\circ C$ $V_R = 0 V$ | | 1.20 1.30 | kA kA |
| | | $t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine | $T_{VJ} = 150^\circ C$ $V_R = 0 V$ | | 1.02 1.10 | kA kA |
| I^2t | value for fusing | $t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine | $T_{VJ} = 45^\circ C$ $V_R = 0 V$ | | 7.20 6.98 | kA^2s kA^2s |
| | | $t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine | $T_{VJ} = 150^\circ C$ $V_R = 0 V$ | | 5.20 5.04 | kA^2s kA^2s |
| C_J | junction capacitance | $V_R = 400 V; f = 1 MHz$ | $T_{VJ} = 25^\circ C$ | | 37 | pF |

| Package PWS-E | | | Ratings | | | |
|---------------|--|------------------------------|---|------|------|--------|
| Symbol | Definition | Conditions | min. | typ. | max. | Unit |
| I_{RMS} | RMS current | per terminal | | | 200 | A |
| T_{stg} | storage temperature | | -40 | | 125 | °C |
| T_{vJ} | virtual junction temperature | | -40 | | 150 | °C |
| Weight | | | | 284 | | g |
| M_D | mounting torque | | 4.25 | | 5.75 | Nm |
| M_T | terminal torque | | 4.25 | | 5.75 | Nm |
| $d_{Spp/App}$ | creepage distance on surface striking distance through air | terminal to terminal | 12.0 | | | mm |
| $d_{Spb/Apb}$ | | terminal to backside | 26.0 | | | mm |
| V_{ISOL} | isolation voltage | t = 1 second t = 1 minute | 3000 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA | 2500 | | V V |



| Ordering | Part Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|--------------|--------------------|---------------|----------|----------|
| Standard | VUO110-18NO7 | VUO110-18NO7 | Box | 5 | 462411 |

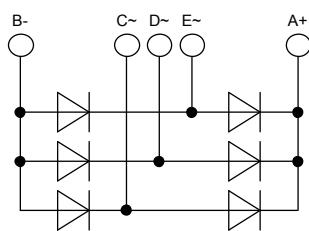
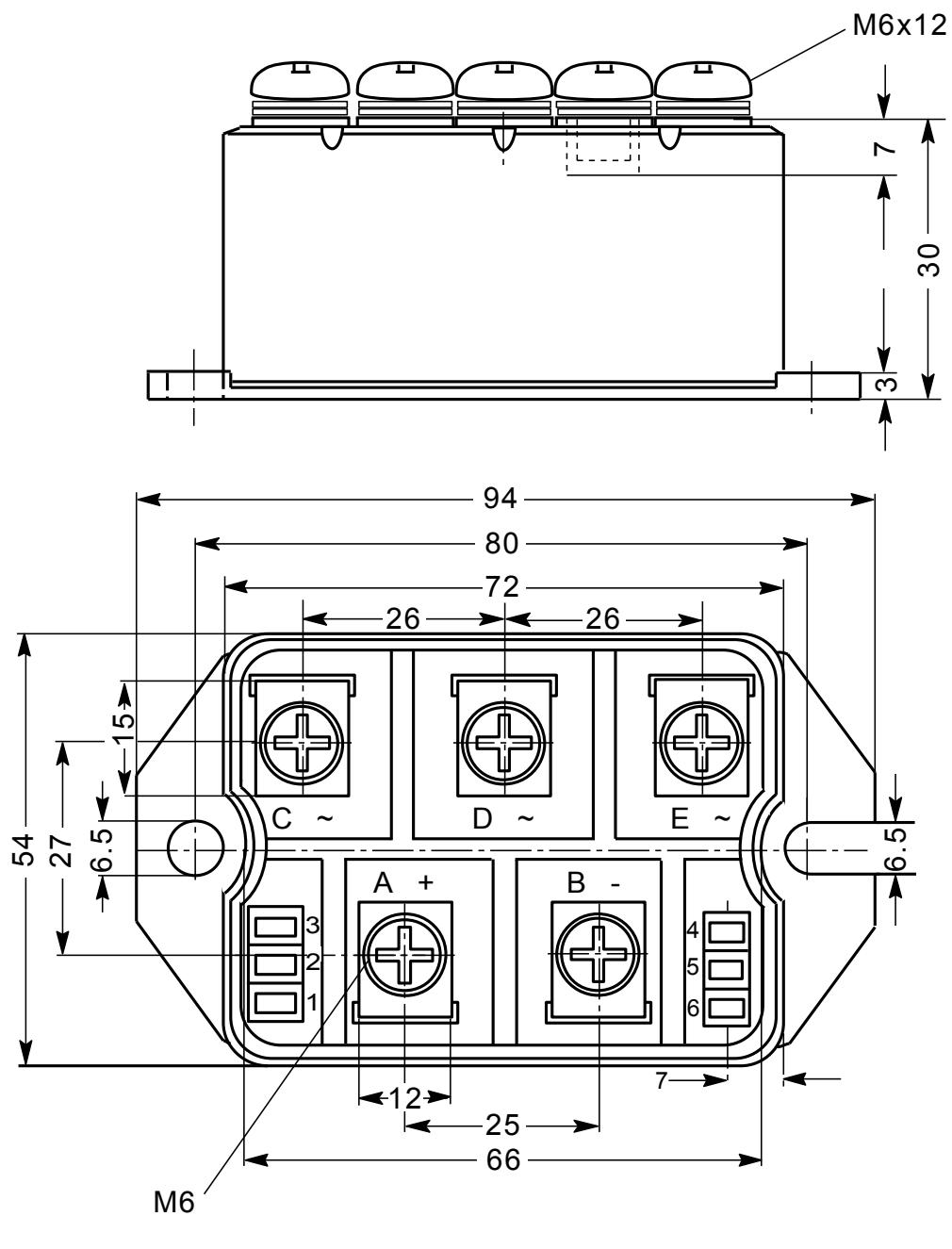
Equivalent Circuits for Simulation

* on die level

$T_{vJ} = 150$ °C

| | | | | |
|-------------|--------------------|-------|-----------|----|
| | V_0 | R_0 | Rectifier | |
| $V_{0\max}$ | threshold voltage | 0.79 | | V |
| $R_{0\max}$ | slope resistance * | 3.3 | | mΩ |

Outlines PWS-E



Rectifier

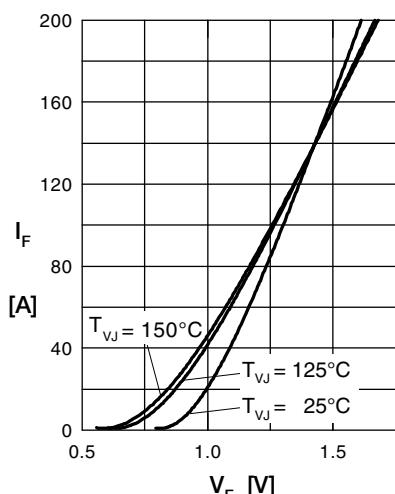


Fig. 1 Forward current vs. voltage drop per diode

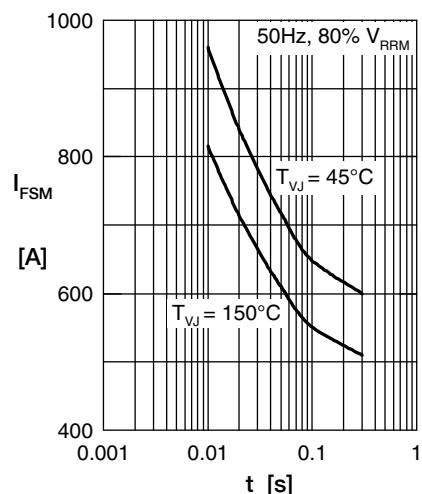


Fig. 2 Surge overload current vs. time per diode

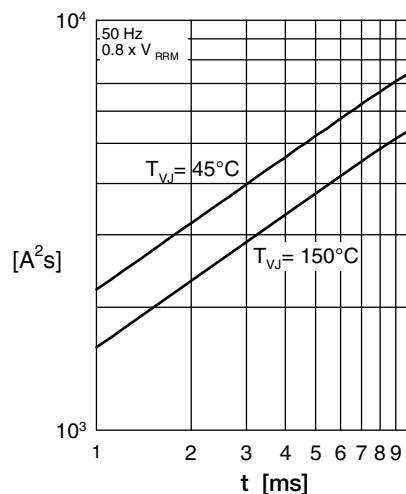
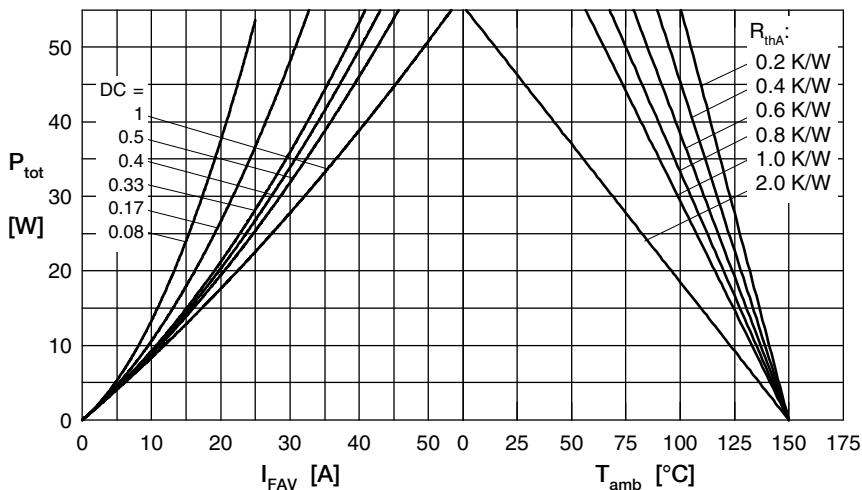
Fig. 3 I^2t vs. time per diode

Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

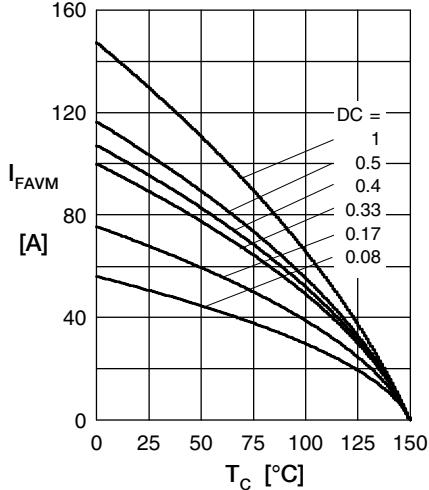


Fig. 5 Max. forward current vs. case temperature per diode

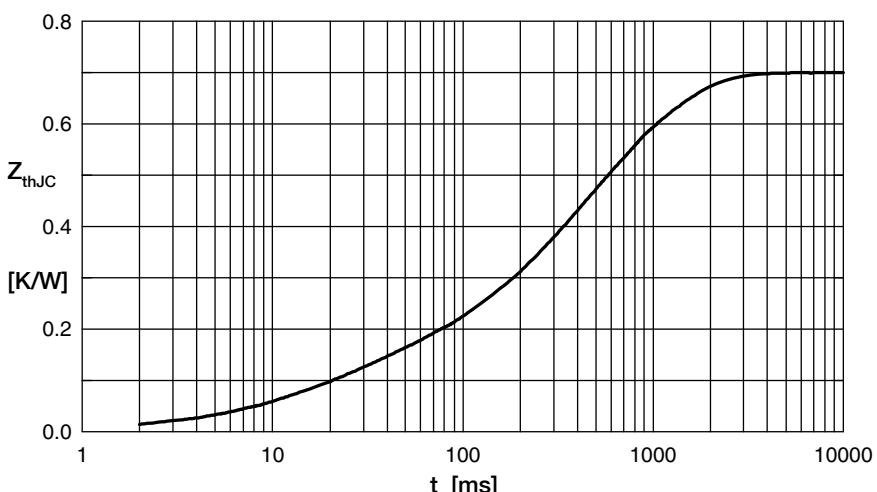


Fig. 6 Transient thermal impedance junction to case vs. time per diode

| R_i | t_i |
|-------|-------|
| 0.100 | 0.020 |
| 0.010 | 0.010 |
| 0.162 | 0.225 |
| 0.258 | 0.800 |
| 0.170 | 0.580 |

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Bridge Rectifiers](#) category:

Click to view products by [IXYS manufacturer:](#)

Other Similar products are found below :

[G3SBA60-E351](#) [GBJ1504-BP](#) [GBU10B-BP](#) [GBU15J-BP](#) [GBU15K-BP](#) [GBU4A-BP](#) [GBU4D-BP](#) [GBU6B-E3/45](#) [GSIB680-E3/45](#) [DB101-BP](#) [DBA100G](#) [DBA150G](#) [DBA20G](#) [DBA250G](#) [DBA40G](#) [DBD10G-TM-E](#) [DBF10G](#) [DBF250G](#) [DBG150G](#) [DBG250G](#) [DF10SA-E345](#) [RMB2S RCG](#) [APT30DF100HJ](#) [APT60DF20HJ](#) [B2S-E3/80](#) [BU1506-E351](#) [BU15085S-E345](#) [BU1508-E3/45](#) [BU1510-E3/45](#) [RS404GL-BP](#) [RS405GL-BP](#) [G3SBA20-E3/51](#) [G5SBA20-E3/51](#) [G5SBA60-E3/51](#) [GBJ1502-BP](#) [GBL02-E351](#) [GBL10-E3/45](#) [GBU10J-BP](#) [GBU4J-BP](#) [GBU4K-BP](#) [GBU8B-E3/45](#) [GBU8D-BP](#) [GBU8J-BP](#) [GSIB1520-E3/45](#) [MB1510](#) [MB352W](#) [MB6M-G](#) [B2M-E345](#) [B40C7000A](#) [B500C7000A](#)